Abstracts

RF W-band wafer-to-wafer transition

K.J. Herrick and L.P.B. Katehi. "RF W-band wafer-to-wafer transition." 2000 MTT-S International Microwave Symposium Digest 00.1 (2000 Vol. I [MWSYM]): 73-76.

Multiwafer silicon designs must provide an avenue for electrical signals to flow from wafer to wafer. For this purpose, a two-layer electrical bond is proposed to provide electrical connection between two coplanar waveguides on vertically stacked silicon wafers. Loss of approximately 0.1 dB is measured for this compact, packaged transition at W-band.

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